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(54) **PHOTOELECTRIC CONVERSION ELEMENT AND SOLAR CELL**

(57) Provided are: a photoelectric conversion element that has a photosensitive layer that includes a light absorbing agent, said light absorbing agent including a compound having a perovskite crystalline structure having a specified cation and anion, wherein at least a portion of the anion that constitutes said compound is an organic anion represented by the formula (An); and a solar cell that uses said photoelectric conversion element. R^1-C(=X^1)-X^2 Formula (An) R^1 represents a hydrogen atom, alkyl group, alkenyl group, alkynyl group, aryl group, heteroaryl group, aliphatic heterocyclic group, -N(R^2)$_2$, -OR^3, -SR^4, and a halogen atom. X^1 represents an O atom or S atom. X^2 represents O^- or S^-. R^2-R^4 are specified groups. In the event that X^1 is an O atom and X^2 is O^-, R^1 is a specified group.

FIG. 1

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Description

BACKGROUND OF THE INVENTION

1. Field of the Invention

[0001] The present invention relates to a photoelectric conversion element and a solar cell.

2. Description of the Related Art

[0002] Photoelectric conversion elements are used in a variety of optical sensors, copiers, solar cells, and the like. It is anticipated that solar cells will be actively put into practical use as cells using non-exhaustible solar energy. Among them, active research and development is underway regarding dye sensitized solar cells in which an organic dye, a Ru bipyridyl complex, or the like is used as a sensitizer, and the photoelectric conversion efficiency thereof reaches approximately 11%.

[0003] Meanwhile, in recent years, research results that solar cells in which a metallic halide is used as a compound having a perovskite-type crystal structure are capable of achieving a relatively high photoelectric conversion efficiency have been reported and attracted attention (for example, WO2014/097299A).

SUMMARY OF THE INVENTION

[0004] Photoelectric conversion elements or solar cells in which a compound having a perovskite-type crystal structure (hereinafter, also referred to as "perovskite compound") is used have attained certain achievements in terms of the improvement of photoelectric conversion efficiencies. However, photoelectric conversion elements or solar cells in which a perovskite compound is used have recently attracted attention and cell performance other than photoelectric conversion efficiencies are barely known.

[0005] For photoelectric conversion elements and solar cells, there is a demand not only for a high photoelectric conversion efficiency but also for durability sufficient to maintain initial performance in on-site environments in which the photoelectric conversion elements and solar cells are actually used. It is known that perovskite compounds are likely to be damaged in highly humid environments, and, for photoelectric conversion elements and solar cells for which a perovskite compound is used, there is a demand for improvement of durability particularly under high-humidity conditions. In addition, in a case in which photoelectric conversion elements and solar cells are put into practical use, there is a demand for suppressing the unevenness of photoelectric conversion performance and stably supplying photoelectric conversion elements and solar cells having uniform qualities.

[0006] An object of the present invention is to provide a photoelectric conversion element in which a perovskite compound is used as a light absorber, moisture resistance is excellent, and manufacturing stability (uniformity in durability (moisture resistance) among elements) is also favorable. In addition, another object of the present invention is to provide a solar cell in which the photoelectric conversion element is used.

[0007] The present inventors found that, in photoelectric conversion elements and solar cells in which a perovskite compound having cations of an element belonging to Group I of the periodic table or organic cations, cations of a metallic atom other than elements belonging to Group I of the periodic table, and anions is used as a light absorber, when specific organic anions are included as at least some of the anions, photoelectric conversion efficiencies do not easily decrease even in highly humid environments and unevenness in durability (moisture resistance) among manufactured elements is also suppressed. The present invention has been completed by repeating studies on the basis of the above-described finding.

[0008] That is, the above-described objects of the present invention have been achieved by the following means.

[1] A photoelectric conversion element comprising: a first electrode having a photosensitive layer including a light absorber on a conductive support; and a second electrode facing the first electrode, in which the light absorber includes a compound having a perovskite-type crystal structure including cations of an element belonging to Group I of the periodic table or organic cations, cations of a metallic atom other than elements belonging to Group I of the periodic table, and anions, and at least some of the anions constituting the compound are organic anions represented by Formula (An),

$$R^1\text{-}C(=X^1)\text{-}X^2 \quad \text{Formula} \qquad (An)$$

In the formula, R^1 represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group,

a heteroaryl group, an aliphatic heterocyclic group, $-N(R^2)_2$, $-OR^3$, $-SR^4$, or a halogen atom. X^1 represents an O atom or a S atom. R^2 to R^4 represent alkyl groups or aryl groups. X^2 represents O^- or S^-.
Here, in a case in which X^1 is an O atom and X^2 is O^-, the alkyl group is a substituted methyl group or an alkyl group having two or more carbon atoms.

[2] The photoelectric conversion element according to [1], in which X^1 represents an O atom, and X^2 represents O^-.

[3] The photoelectric conversion element according to [1] or [2], in which R^1 is an aryl group or a heteroaryl group.

[4] The photoelectric conversion element according to any one of [1] to [3], in which the compound having a perovskite-type crystal structure has anions of a halogen atom.

[5] The photoelectric conversion element according to [4], in which, in the compound having a perovskite-type crystal structure, a molar ratio of the anions of a halogen atom to the organic anions represented by Formula (An) satisfies the following expression,

$$32 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331.$$

[6] The photoelectric conversion element according to [5], in which, in the compound having a perovskite-type crystal structure, the molar ratio of the anions of a halogen atom to the organic anions represented by Formula (An) satisfies the following expression,

$$54 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331.$$

[7] A solar cell using the photoelectric conversion element according to any one of [1] to [6].

[0009] In the present specification, regarding individual chemical formulae, there are cases in which a part of the chemical formula is expressed as a rational formula for understanding of the chemical structures of perovskite compounds. Accordingly, in the individual chemical formulae, partial structures are called groups (substituents), ions, atoms, or the like; however, in the present specification, there are cases in which the partial structures will refer to element groups or elements constituting groups (substituents) or ions represented by the above-illustrated formulae in addition to groups (substituents), ions, atoms, or the like.

[0010] In the present specification, the expression of compounds is used to indicate not only the compounds themselves but also salts or ions thereof. Furthermore, groups or compounds that are not clearly described as being substituted or unsubstituted refer to groups or compounds having an arbitrary substituent as long as desired effects are exhibited.

[0011] In the present specification, when there are a plurality of substituents and the like expressed using a specific reference symbol or a plurality of substituents and the like are specified at the same time, the respective substituents and the like may be identical to or different from each other unless particularly otherwise described. What has been described above is also true for the specification regarding the number of substituents and the like. In addition, rings, for example, alicycles, aromatic rings, and hetero rings may be further fused together and thus form a fused ring.

[0012] In the present specification, unless particularly otherwise described, the term "groups" also refer to groups having a substituent. For example, "alkyl groups" refer to both substituted alkyl groups and unsubstituted alkyl.

[0013] In addition, in the present specification, numerical ranges expressed using "to" include numerical values before and after the "to" as the lower limit value and the upper limit value.

[0014] The photoelectric conversion element and the solar cell of the present invention are excellent in terms of moisture resistance and also excellent in terms of manufacturing stability (uniformity in durability (moisture resistance) among elements) while having a constitution in which a perovskite compound is provided as a light absorber.

[0015] The above-described and other characteristics and advantages of the present invention will be further clarified from the following description with appropriate reference to the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0016]

Fig. 1 is a cross sectional view schematically illustrating a preferred aspect of a photoelectric conversion element of the present invention.

Fig. 2 is a cross sectional view schematically illustrating a preferred aspect of the photoelectric conversion element of the present invention including a thick photosensitive layer.

Fig. 3 is a cross sectional view schematically illustrating another preferred aspect of the photoelectric conversion

element of the present invention.

Fig. 4 is a cross sectional view schematically illustrating still another preferred aspect of the photoelectric conversion element of the present invention.

Fig. 5 is a cross sectional view schematically illustrating far still another preferred aspect of the photoelectric conversion element of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

«Photoelectric conversion element»

[0017] A photoelectric conversion element of the present invention has a first electrode having a conductive support and a photosensitive layer including a light absorber and a second electrode facing the first electrode. Here, the first electrode and the second electrode facing each other refers to both of an aspect in which the first electrode and the second electrode are laminated in a state of being in contact with each other and an aspect in which the first electrode and the second electrode are laminated through another layer (that is, an aspect in which the first electrode and the second electrode are provided so as to face each other while the first electrode and the second electrode sandwich another layer).

[0018] The photoelectric conversion element of the present invention preferably has a hole transport layer provided between the first electrode and the second electrode. The photosensitive layer and the second electrode are provided in this order on the conductive support. That is, in a case in which the photoelectric conversion element has the hole transport layer, the photosensitive layer, the hole transport layer, and the second electrode are preferably provided on the conductive support in this order.

[0019] In addition, the hole transport layer may be provided between the conductive support and the photosensitive layer. In this case, the hole transport layer, the photosensitive layer, and the second electrode are provided on the conductive support in this order.

[0020] The light absorber includes at least one perovskite compound described below. The light absorber may also include a light absorber other than the perovskite compound together with the perovskite compound. Examples of the light absorber other than the perovskite compound include metallic complex dyes and organic dyes.

[0021] In the present invention, "the photosensitive layer being provided on the conductive support" means that the photosensitive layer is provided in contact with the surface of the conductive support or the photosensitive layer is provided above the surface of the conductive support through another layer.

[0022] In the aspect in which the photosensitive layer is provided above the surface of the conductive support through another layer, examples of the layer provided between the conductive support and the photosensitive layer include a porous layer, a blocking layer, an electron transport layer, a hole transport layer, and the like.

[0023] In the present invention, examples of the aspect in which the photosensitive layer is provided above the surface of the conductive support through another layer include an aspect in which the photosensitive layer is provided on the surface of a porous layer in a thin film shape or the like (refer to Fig. 1), an aspect in which the photosensitive layer is provided to be thick on the surface of a porous layer (refer to Fig. 2), an aspect in which the photosensitive layer is provided to be thin on the surface of a blocking layer, an aspect in which the photosensitive layer is provided on the surface of a blocking layer in a thick film shape (refer to Fig. 3), an aspect in which the photosensitive layer is provided on the surface of an electron transport layer in a thin film shape or thick film shape (refer to Fig. 4), and an aspect in which the photosensitive layer is provided on the surface of a hole transport layer in a thin film shape or thick film shape (refer to Fig. 5). The photosensitive layer may be provided in a linear shape or in a dispersed pattern, but is preferably provided in a film shape.

[0024] There is no particular limitation regarding constitutions other than constitutions specified in the present invention for the photoelectric conversion element of the present invention, and well-known constitutions relating to photoelectric conversion elements and solar cells can be employed. Individual layers constituting the photoelectric conversion element of the present invention are designed according to their purposes and may be formed in, for example, a monolayer or multilayers.

[0025] Hereinafter, preferred aspects of the photoelectric conversion element of the present invention will be described.

[0026] In Figs. 1 to 5, the same reference symbol indicates the same constituent element (member).

[0027] Meanwhile, in Figs. 1 and 2, fine particles forming a porous layer 12 are illustrated in an enlarged manner. These fine particles are preferably jammed with each other (accumulated or in close contact with each other) in the horizontal direction and the vertical direction with respect to a conductive support 11 and thus form a porous structure.

[0028] In the present specification, in the case of being simply described, a "photoelectric conversion element 10" refers to photoelectric conversion elements 10A, 10B, 10C, 10D, and 10E unless particularly otherwise described. This is also true for a system 100 and a first electrode 1. In addition, in the case of being simply described, a "photosensitive layer 13" refers to photosensitive layers 13A, 13B, and 13C unless particularly otherwise described. Similarly, in the

case of being described as a "hole transport layer 3", the "hole transport layer 3" refers to hole transport layers 3A and 3B unless particularly otherwise described.

[0029] Examples of the preferred aspects of the photoelectric conversion element of the present invention include the photoelectric conversion element 10A illustrated in Fig. 1. A system 100A illustrated in Fig. 1 is a system in which the photoelectric conversion element 10A is applied as a cell that causes action means M (for example, an electric motor) to operate through an external circuit 6.

[0030] The photoelectric conversion element 10A includes a first electrode 1A, a second electrode 2, and the hole transport layer 3A including a hole-transporting material described below between the first electrode 1A and the second electrode 2.

[0031] The first electrode 1A includes the conductive support 11 made up of a support 11a and a transparent electrode 11b, the porous layer 12, and the photosensitive layer 13A on the porous layer 12. In addition, a blocking layer 14 is provided on the transparent electrode 11b, and the porous layer 12 is formed on the blocking layer 14. In the photoelectric conversion element 10A including the porous layer 12 as described above, since the surface area of the photosensitive layer 13A increases, it is assumed that the charge separation and charge transfer efficiency improves.

[0032] The photoelectric conversion element 10B illustrated in Fig. 2 is a schematic illustration of a preferred aspect in which the photosensitive layer 13A in the photoelectric conversion element 10A illustrated in Fig. 1 is provided to be thick. In this photoelectric conversion element 10B, the hole transport layer 3B is provided to be thin. The photoelectric conversion element 10B is different from the photoelectric conversion element 10A illustrated in Fig. 1 in terms of the film thicknesses of the photosensitive layer 13B and the hole transport layer 3B, but is constituted in the same manner as the photoelectric conversion element 10A except for the film thicknesses.

[0033] The photoelectric conversion element 10C illustrated in Fig. 3 is a schematic illustration of another preferred aspect of the photoelectric conversion element of the present invention. The photoelectric conversion element 10C is different from the photoelectric conversion element 10B illustrated in Fig. 2 in terms of the porous layer 12 not being provided, but is constituted in the same manner as the photoelectric conversion element 10B except for what has been described above. That is, in the photoelectric conversion element 10C, the photosensitive layer 13C is formed on the surface of the blocking layer 14 in a thick film shape.

[0034] The photoelectric conversion element 10D illustrated in Fig. 4 is a schematic illustration of still another preferred aspect of the photoelectric conversion element of the present invention. The photoelectric conversion element 10D is different from the photoelectric conversion element 10C illustrated in Fig. 3 in terms of the provision of an electron transport layer 15 instead of the blocking layer 14, but is constituted in the same manner as the photoelectric conversion element 10C except for what has been described above. The first electrode ID has the conductive support 11 and the electron transport layer 15 and the photosensitive layer 13C which are sequentially formed on the conductive support 11. This photoelectric conversion element 10D is preferred since the respective layers can be formed using organic materials. Therefore, the productivity of the photoelectric conversion element improves, and furthermore, thickness reduction or flexibilization becomes possible.

[0035] The photoelectric conversion element 10E illustrated in Fig. 5 is a schematic illustration of far still another preferred aspect of the photoelectric conversion element of the present invention. A system 100E including the photoelectric conversion element 10E is, similar to the system 100A, a system that is applied as a cell.

[0036] The photoelectric conversion element 10E has a first electrode 1E, the second electrode 2, and the electron transport layer 4 between the first electrode 1E and the second electrode 2. The first electrode I E has the conductive support 11 and the hole transport layer 16 and the photosensitive layer 13C which are sequentially formed on the conductive support 11. This photoelectric conversion element 10E is preferred since, similar to the photoelectric conversion element 10D, the respective layers can be formed using organic materials.

[0037] In the present invention, the system 100 to which the photoelectric conversion element 10 is applied functions as a solar cell in the following manner.

[0038] That is, in the photoelectric conversion element 10A, light that has passed through the conductive support 11 or the second electrode 2 and has entered the photosensitive layer 13 excites a light absorber. The excited light absorber has high-energy electrons and is capable of emitting the electrons. The light absorber which has emitted high-energy electrons turns into an oxidant.

[0039] In the photoelectric conversion elements 10A to 10D, electrons emitted from the light absorber migrate among the light absorber particles and reach the conductive support 11. At this time, the light absorber that has emitted electrons having a high energy turns into an oxidant. The electrons that have reached the conductive support 11 do their work in the external circuit 6 and then return to the photosensitive layer 13 through the second electrode 2 (in a case in which the hole transport layer 3 is provided, through the hole transport layer 3 in addition to the second electrode). The light absorber is reduced by the electrons which have returned to the photosensitive layer 13.

[0040] Meanwhile, in the photoelectric conversion element 10E, electrons emitted from the light absorber reach the second electrode 2 from the photosensitive layer 13C through the electron transport layer 4, do their work in the external circuit 6, and then return to the photosensitive layer 13 through the conductive support 11. The light absorber is reduced

by the electrons which have returned to the photosensitive layer 13.

[0041] In the photoelectric conversion element 10, the system 100 functions as a solar cell by repeating the cycle of the above-described excitation of the light absorber and electron migration.

[0042] In the photoelectric conversion elements 10A to 10D, the flow direction of electrons from the photosensitive layer 13 to the conductive support 11 varies depending on the presence or absence, kind, and the like of the porous layer 12. In the photoelectric conversion element 10 of the present invention, electron conduction in which electrons migrate among the light absorber particles occurs. Therefore, in a case in which the porous layer 12 is provided, the porous layer 12 can be formed of an insulating body other than semiconductors in the related art. In a case in which the porous layer 12 is formed of a semiconductor, electron conduction in which electrons migrate inside or among semiconductor fine particles in the porous layer 12 also occurs. On the other hand, in a case in which the porous layer 12 is formed of an insulating body, electron conduction does not occur in the porous layer 12. In a case in which the porous layer 12 is formed of an insulating body, and aluminum oxide (Al_2O_3) fine particles are used as insulating body fine particles, a relatively high electromotive force (Voc) is obtained.

[0043] Meanwhile, in a case in which the blocking layer 14, like other layers, is formed of a conductor or a semiconductor as well, electron conduction occurs in the blocking layer 14.

[0044] In addition, electron conduction occurs even in the electron transport layer 15.

[0045] The photoelectric conversion element and the solar cell of the present invention are not limited to the above-described preferred aspects, and the constitutions and the like of the respective aspects can be appropriately combined together within the scope of the gist of the present invention.

[0046] In the present invention, materials and the respective members which are used in the photoelectric conversion element and the solar cell can be prepared using ordinary methods except for the light absorber. Regarding photoelectric conversion elements or solar cells in which the perovskite compound is used, it is possible to refer to, for example, WO2014/097299A. In addition, regarding dye sensitized solar cells, it is possible to refer to, for example, JP2001-291534A, the specification of US4927721A, the specification of US4684537A, the specification of US5084365A, the specification of US5350644A, the specification of US5463057A, the specification of US5525440A, JP1995-249790A (JP-H7-249790A), JP2004-220974A, and JP2008-135197A.

[0047] Hereinafter, preferred aspects of the main members and compounds of the photoelectric conversion element and the solar cell of the present invention will be described.

<First electrode 1>

[0048] The first electrode 1 includes the conductive support 11 and the photosensitive layer 13 and functions as a working electrode in the photoelectric conversion element 10.

[0049] As illustrated in Figs. 1 to 5, the first electrode 1 preferably includes the porous layer 12, the blocking layer 14, and at least one layer of the electron transport layer 15 or the hole transport layer 16.

[0050] The first electrode 1 preferably includes at least the blocking layer 14 in terms of short circuit prevention and more preferably includes the porous layer 12 and the blocking layer 14 in terms of light absorption efficiency and short circuit prevention.

[0051] In addition, the first electrode 1 preferably includes the electron transport layer 15 or the hole transport layer 16 since the first electrode can be formed of an organic material.

- Conductive support 11 -

[0052] The conductive support 11 is not particularly limited as long as the conductive support is conductive and is capable of supporting the photosensitive layer 13 or the like. The conductive support 11 preferably has a constitution in which the conductive support is formed of a conductive material, for example, metal or a constitution in which the glass or plastic support 11a and the transparent electrode 11b formed on the surface of the support 11a as a conductive film are provided.

[0053] Among these, the conductive support 11 in which a film of the transparent electrode 11b is formed by applying a conductive metallic oxide onto the surface of the glass or plastic support 11a as illustrated in Figs. 1 to 5 is more preferred. Examples of the support 11a formed of plastic include transparent polymer films described in Paragraph 0153 of JP2001-291534A. As a material used to form the support 11a, it is possible to use, in addition to glass or plastic, ceramics (JP2005-135902A) or conductive resins (JP2001-160425A). The metallic oxide is preferably a tin oxide (TO) and particularly preferably an indium-tin oxide (a tin-doped indium oxide, ITO) or a fluorine-doped tin oxide such as a fluorine-doped tin oxide (FTO). At this time, the amount of the metallic oxide applied is preferably 0.1 to 100 g per square meter of the surface area of the support 11 a. In a case in which the conductive support 11 is used, light preferably enters the conductive support through the support 11a side.

[0054] The conductive support 11 is preferably substantially transparent. In the present invention, "being substantially

transparent" means that the transmittance of light (having a wavelength of 300 to 1,200 nm) is 10% or higher, preferably 50% or higher, and particularly preferably 80% or higher.

[0055] The thicknesses of the support 11a and the conductive support 11 are not particularly limited and are set to appropriate thicknesses. For example, the thicknesses are preferably 0.01 μm to 10 mm, more preferably 0.1 μm to 5 mm, and particularly preferably 0.3 μm to 4 mm.

[0056] In a case in which the transparent electrode 11b is provided, the film thickness of the transparent electrode 11b is not particularly limited and is, for example, preferably 0.01 to 30 μm, more preferably 0.03 to 25 μm, and particularly preferably 0.05 to 20 μm.

[0057] The conductive support 11 or the support 11a may have a light management function on the surface. For example, the conductive support 11 or the support 11a may have on the surface an antireflection film obtained by alternately laminating high-refractive index films and low-refractive index oxide films which is described in JP2003-123859A or may have a light guide function described in JP2002-260746A.

- Blocking layer 14 -

[0058] In the present invention, as in the photoelectric conversion elements 10A to 10C, the blocking layer 14 is preferably provided on the surface of the transparent electrode 11b, that is, between the conductive support 11 and the porous layer 12, the photosensitive layer 13, the hole transport layer 3, or the like.

[0059] In the photoelectric conversion element and the solar cell, for example, in a case in which the photosensitive layer 13 or the hole transport layer 3 and the transparent electrode 11b are electrically connected with each other, reverse currents are generated. The blocking layer 14 performs a function of preventing these reverse currents. The blocking layer 14 is also referred to as a short circuit prevention layer.

[0060] The blocking layer may also be provided in a case in which the photoelectric conversion element includes an electron transport layer. For example, in the case of the photoelectric conversion element 10D, the blocking layer may be provided between the conductive support 11 and the electron transport layer 15, and in the case of the photoelectric conversion element 10E, the blocking layer may be provided between the second electrode 2 and the electron transport layer 4.

[0061] A material used to form the blocking layer 14 is not particularly limited as long as the material is capable of performing the above-described function, but is preferably a substance which transmits visible light and is insulating with respect to the conductive support 11 (the transparent electrode 11b). The "substance insulating with respect to the conductive support 11 (the transparent electrode 11b)" specifically refers to a compound having an energy level of the conduction band which is equal to or higher than the energy level of the conduction band of a material used to form the conductive support 11 (a metallic oxide used to form the transparent electrode 11b) and is lower than the energy level of the conduction band of a material constituting the porous layer 12 or the ground state of the light absorber (n-type semiconductor compound).

[0062] Examples of a material used to form the blocking layer 14 include silicon oxide, magnesium oxide, aluminum oxide, calcium carbonate, polyvinyl alcohols, polyurethanes, and the like. In addition, the material may be a material that is ordinarily used as a photoelectric conversion material, and examples thereof include titanium oxide, tin oxide, niobium oxide, tungsten oxide, and the like. Among these, titanium oxide, tin oxide, magnesium oxide, aluminum oxide, and the like are preferred.

[0063] The film thickness of the blocking layer 14 is preferably 0.001 to 10 μm, more preferably 0.005 to 1 μm, and particularly preferably 0.01 to 0.1 μm.

[0064] In the present invention, the film thicknesses of the respective layers can be measured by observing cross sections of the photoelectric conversion element 10 using a scanning electron microscope (SEM) or the like.

-Porous layer 12-

[0065] In the present invention, as in the photoelectric conversion elements 10A and 10B, the porous layer 12 is preferably provided on the transparent electrode 11b. In a case in which the photoelectric conversion element includes the blocking layer 14, the porous layer 12 is preferably formed on the blocking layer 14.

[0066] The porous layer 12 is a layer that functions as a scaffold for carrying the photosensitive layer 13 on the surface. In solar cells, in order to increase the light absorption efficiency, it is preferable to increase the surface area of at least a portion receiving light such as sunlight, and it is preferable to increase the surface area of the porous layer 12 as a whole.

[0067] The porous layer 12 is preferably a fine particle layer having pores which is formed of fine particles of a material used to form the porous layer 12 being accumulated or in close contact with each other. The porous layer 12 may be a fine particle layer formed of two or more kinds of many fine particles being accumulated together. In a case in which the porous layer 12 is a fine particle layer having pores, it is possible to increase the amount of the light absorber carried (adsorption amount).

[0068] In order to increase the surface area of the porous layer 12, it is preferable to increase the surface area of individual fine particles that constitute the porous layer 12. In the present invention, the surface area of fine particles used to form the porous layer 12 in a state in which the fine particles are applied onto the conductive support 11 and the like is preferably 10 or more times and more preferably 100 or more times the projected area. The upper limit thereof is not particularly limited, but is, generally, approximately 5,000 times. Regarding the particle diameters of the fine particles used to form the porous layer 12, the average particle diameter of the diameters of equivalent circles of the projected areas is preferably 0.001 to 1 μm for the primary particles. In a case in which the porous layer 12 is formed using a dispersion of the fine particles, the average particle diameter of the fine particles is preferably 0.01 to 100 μm in terms of the average particle diameter in the dispersion.

[0069] For the material used to form the porous layer 12, there is no particular limitation regarding conductivity, and thus the material may be an insulating body (insulating material), a conductive material, or a semiconductor (semi-conductive material).

[0070] As the material used to form the porous layer 12, it is possible to use, for example, chalcogenides (for example, oxides, sulfides, selenides, and the like) of metal, compounds having a perovskite-type crystal structure (except for light absorbers described below), oxides of silicon (for example, silicon dioxide and zeolite), or carbon nanotubes (including carbon nanowires, carbon nanorods, and the like).

[0071] The chalcogenides of metal are not particularly limited, and preferred examples thereof include individual oxides of titanium, tin, zinc, tungsten, zirconium, hafnium, strontium, indium, cerium, yttrium, lanthanum, vanadium, niobium, aluminum, or tantalum, cadmium sulfide, cadmium selenide, and the like. Examples of the crystal structure of the chalcogenides of metal include an anatase-type crystal structure, a brookite-type crystal structure, and a rutile-type crystal structure, and an anatase-type crystal structure and a brookite-type crystal structure are preferred.

[0072] The compounds having a perovskite-type crystal structure are not particularly limited, and examples thereof include transition metal oxides and the like. Examples thereof include strontium titanate, calcium titanate, barium titanate, lead titanate, barium zirconate, barium stannate, lead zirconate, strontium zirconate, strontium tantalate, potassium niobate, bismuth ferrate, barium strontium titanate, lanthanum barium titanate, calcium titanate, sodium titanate, and bismuth titanate. Among these, strontium titanate, calcium titanate, and the like are preferred.

[0073] The carbon nanotubes have a shape obtained by rolling a carbon film (graphene sheet) in a tubular shape. Carbon nanotubes are classified into single-walled carbon nanotubes (SWCNT) obtained by coiling one graphene sheet in a cylindrical shape, double-walled carbon nanotubes (DWCNT) obtained by coiling two graphene sheets in a concentric shape, and multi-walled carbon nanotubes (MWCNT) obtained by coiling multiple graphene sheets in a concentric shape. As the porous layer 12, any carbon nanotubes can be used without any particular limitation.

[0074] Among these, the material used to form the porous layer 12 is preferably an oxide of titanium, tin, zinc, zirconium, aluminum, or silicon or a carbon nanotube and more preferably titanium oxide or aluminum oxide.

[0075] The porous layer 12 may be formed of at least one of the chalcogenide of metal, the compound having a perovskite-type crystal structure, the oxide of silicon, or the carbon nanotube or may be formed of a plurality thereof.

[0076] The film thickness of the porous layer 12 is not particularly limited and is generally in a range of 0.1 to 100 μm, and, in the case of being used as a solar cell, the film thickness is preferably 0.1 to 50 μm and more preferably 0.2 to 30 μm.

- Electron transport layer 15 -

[0077] In the present invention, as in the photoelectric conversion element 10D, the electron transport layer 15 is preferably provided on the surface of the transparent electrode 11b.

[0078] The electron transport layer 15 has a function of transporting electrons generated in the photosensitive layer 13 to the conductive support 11. The electron transport layer 15 is formed of an electron-transporting material capable of exhibiting the above-described function. The electron-transporting material is not particularly limited and is preferably an organic material (organic electron-transporting material). Examples of the organic electron-transporting material include fullerene compounds such as [6,6]-phenyl-C61-butyric acid methyl ester (PCBM), perylene compounds such as perylene tetracarboxylic diimide (PTCDI), additionally, low-molecular-weight compounds such as tetracyanoquinodimethane (TCNQ), high-molecular-weight compounds, and the like.

[0079] The film thickness of the electron transport layer 15 is not particularly limited and is preferably 0.001 to 10 μm and more preferably 0.01 to 1 μm.

- Hole transport layer 16 -

[0080] In the present invention, as in the photoelectric conversion element 10E, the hole transport layer 16 is preferably provided on the surface of the transparent electrode 11b.

[0081] The hole transport layer 16 is the same as the hole transport layer 3 described below except for the fact that the hole transport layer is formed at a different location.

- Photosensitive layer (light-absorbing layer) 13 -

[0082] In the photosensitive layer 13, a perovskite compound described below is preferably provided as a light absorber on the surface (including the inner surfaces in a case in which surfaces provided with the photosensitive layer 13 are uneven) of each of the porous layer 12 (in the photoelectric conversion elements 10A and 10B), the blocking layer 14 (in the photoelectric conversion element 10C), the electron transport layer 15 (in the photoelectric conversion element 10D), and the hole transport layer 16 (in the photoelectric conversion element 10E).

[0083] In the present invention, the light absorber needs to contain at least one perovskite compound described below and may contain two or more perovskite compounds.

[0084] The photosensitive layer 13 may be a single layer or a laminate of two or more layers. In a case in which the photosensitive layer 13 is a laminate structure of two or more layers, the laminate structure may be a laminate of layers made of mutually different light absorbers or may have an interlayer including a hole-transporting material laminated between the photosensitive layer and the photosensitive layer.

[0085] A form of the photosensitive layer 13 being present on the conductive support 11 is as described above. The photosensitive layer 13 is preferably provided on the surface of each of the above-described layers so that excited electrons flow into the conductive support 11. At this time, the photosensitive layer 13 may be provided on the entire surface or on a part of the surface of the above-described layers.

[0086] The film thickness of the photosensitive layer 13 is appropriately set according to aspects of the photosensitive layer 13 provided on the conductive support 11 and is not particularly limited. The film thickness of the photosensitive layer 13 (in a case in which the porous layer 12 is provided, the total film thickness including the film thickness of the porous layer 12) is, for example, preferably 0.1 to 100 μm, more preferably 0.1 to 50 μm, and particularly preferably 0.2 to 30 μm.

[0087] In the present invention, in a case in which the photosensitive layer is provided in a thick film shape (the photosensitive layers 13B and 13C), the light absorber included in the photosensitive layer also functions as a hole-transporting material.

[Light absorber in photosensitive layer]

[0088] The photosensitive layer 13 includes, as a light absorber, a perovskite compound having cations of an element belonging to Group I of the periodic table or organic cations, cations of metallic atoms other than elements belonging to Group I of the periodic table, and anions including specific organic anions.

[0089] The cations of an element belonging to Group I of the periodic table that the perovskite compound being used in the present invention may have are preferably lithium ions (Li^+), sodium ions (Na^+), potassium ions (K^+), or cesium ions (Cs^+), and, among these, Cs^+ is more preferred.

[0090] The organic cations that the perovskite compound being used in the present invention may have are not particularly limited as long as the organic cations are cations of an organic group having the above-described properties, but are preferably an organic cation represented by Formula (1).

$$R^A\text{-}NH_3^+ \qquad \text{Formula (1)}$$

[0091] In the formula, R^A represents a substituent. R^A is preferably an alkyl group, a cycloalkyl group, a cycloalkenyl group, a cyclodienyl group, an alkenyl group, an alkynyl group, an aryl group, a heteroaryl group, or a group that can be represented by Formula (2). Among these, an alkyl group, and the group that can be represented by Formula (2) are more preferred.

Formula (2)

[0092] In the formula, X^a represents NR^{1c}, an oxygen atom, or a sulfur atom. R^{1b} and R^{1c} each independently represent a hydrogen atom or a substituent. * represents a bonding location with an N atom in Formula (1).

[0093] An organic ammonium cation formed by bonding R^A and NH_3^+ which is represented by Formula (1) may have a resonance structure. For example, in a case in which X^a in the group that can be represented by Formula (2) is NH (R^{1c} is a hydrogen atom), examples of the organic cation include not only organic ammonium cations formed by bonding the group that can be represented by Formula (2) and NH_3^+ but also organic amidinium cations which are one of the

resonance structures of the organic ammonium cation. Examples of the organic amidinium cations include cations represented by Formula (A^{am}). Meanwhile, in the present specification, there are cases in which the cations represented by Formula (A^{am}) are expressed as "$R^{1b}C(=NH)-NH_3$" for convenience.

Formula (A^{am})

[0094] Examples of the alkyl group that can be employed as R^A include linear alkyl groups and branched alkyl groups. The number of carbon atoms in the alkyl group is preferably 1 to 18, more preferably 1 to 6, and still more preferably 1 to 3. Specific examples of preferred alkyl groups include methyl, ethyl, propyl, isopropyl, n-butyl, t-butyl, pentyl, and hexyl.

[0095] In the cycloalkyl group that can be employed as R^A, the number of carbon atoms is preferably 3 to 8. Specific examples of preferred cycloalkyl groups include cyclopropyl, cyclopentyl, and cyclohexyl.

[0096] In the cycloalkenyl group that can be employed as R^A, the number of carbon atoms is preferably 3 to 8, more preferably 4 to 6, and still more preferably 5 or 6. Specific examples of preferred cycloalkenyl groups include a cyclobutenyl group, a cyclopentenyl group, a cyclohexynyl group, a cycloheptenyl group, and a cyclooctenyl group.

[0097] In the cyclodienyl group that can be employed as R^A, the number of carbon atoms is preferably 5 to 10, more preferably 5 to 8, and still more preferably 5 or 6. Specific examples of preferred cyclodienyl groups include a cyclopentadienyl group and a cyclohexadienyl group.

[0098] Examples of the alkenyl group that can be employed as R^A include linear alkenyl groups and branched alkenyl groups. The number of carbon atoms in the alkenyl group is preferably 2 to 18, more preferably 2 to 7, still more preferably 2 to 6, and particularly preferably 2 to 5. Specific examples of preferred alkenyl groups include vinyl, allyl, butenyl, and hexenyl.

[0099] Examples of the alkynyl group that can be employed as R^A include linear alkynyl groups and branched alkynyl groups. The number of carbon atoms in the alkynyl group is preferably 2 to 18, more preferably 2 to 7, still more preferably 2 to 5, and particularly preferably 2 to 4. Specific examples of preferred alkynyl groups include ethynyl, butynyl, and hexynyl.

[0100] The aryl group that can be employed as R^A is preferably an aryl group having 6 to 14 carbon atoms and more preferably an aryl group having 6 to 12 carbon atoms. Specific examples of preferred aryl groups include phenyl and naphthyl, and phenyl is still more preferred.

[0101] Examples of the heteroaryl group that can be employed as R^A include groups formed of an aromatic hetero ring alone and groups formed of a condensed hetero ring obtained by condensing another ring, for example, an aromatic ring, an aliphatic ring, or a hetero ring with the aromatic hetero ring.

[0102] The ring-constituting hetero atom constituting the aromatic hetero ring is preferably a nitrogen atom, an oxygen atom, or a sulfur atom. In addition, regarding the number of ring members of the aromatic hetero ring, five-membered rings or six-membered rings are preferred.

[0103] Examples of the five-membered aromatic hetero ring and the condensed hetero ring including the five-membered aromatic hetero ring include a pyrrole ring, an imidazole ring, a pyrazole ring, an oxazole ring, a thiazole ring, a triazole ring, a furan ring, a thiophene ring, a benzimidazole ring, a benzoxazole ring, a benzothiazole ring, an indoline ring, and an indazole ring. In addition, examples of the six-membered aromatic hetero ring and the condensed hetero ring including the six-membered aromatic hetero ring include a pyridine ring, a pyrimidine ring, a pyrazine ring, a triazine ring, a quinoline ring, and a quinazoline ring.

[0104] In the group that can be represented by Formula (2), X^a represents NR^{1c}, an oxygen atom, or a sulfur atom and is preferably NR^{1c}. Here, R^{1c} represents a hydrogen atom or substituent and is preferably a hydrogen atom, an alkyl group, a cycloalkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and more preferably a hydrogen atom.

[0105] R^{1b} represents a hydrogen atom or a substituent and is preferably a hydrogen atom. Examples of a substituent that R^{1b} may have include an amino group, an alkyl group, a cycloalkyl group, an alkenyl group, an alkynyl group, an aryl group, and a heteroaryl group.

[0106] An alkyl group, a cycloalkyl group, an alkenyl group, an alkynyl group, an aryl group, and a heteroaryl group that can be respectively employed by R^{1b} and R^{1c} are the same as the alkyl group, the cycloalkyl group, the alkenyl group, the alkynyl group, the aryl group, and the heteroaryl group that can be respectively employed by R^A in Formula (1) respectively, and preferred groups are also identical thereto.

[0107] Examples of the group that can be represented by Formula (2) include a (thio)acyl group, a (thio)carbamoyl

group, an imidoyl group, and an amidino group.

[0108] Examples of the (thio)acyl group include an acyl group and a thioacyl group. The acyl group is preferably an acyl group having a total of 1 to 7 carbon atoms, and examples thereof include formyl, acetyl ($CH_3C(=O)$-), propionyl, hexanoyl, and the like. The thioacyl group is preferably a thioacyl group having a total of 1 to 7 carbon atoms, and examples thereof include thioformyl, thioacetyl ($CH_3C(=S)$-), thiopropionyl, and the like.

[0109] Examples of the (thio)carbamoyl group include a carbamoyl group ($H_2NC(=O)$-) and thiocarbamoyl group ($H_2NC(=S)$-).

[0110] The imidoyl group is a group represented by R^{1b}-$C(=NR^{1c})$-, R^{1b} and R^{1c} each are preferably a hydrogen atom or an alkyl group, and the alkyl group is more preferably the same as the alkyl group as R^{1a}. Examples thereof include formimidoyl ($HC(=NH)$-), acetoimidoyl ($CH_3C(=NH)$-), propionimidoyl ($CH_3CH_2C(=NH)$-), and the like. Among these, formimidoyl is preferred.

[0111] The amidino group as the group that can be represented by Formula (2) has a structure in which R^{1b} of the imidoyl group is an amino group and R^{1c} is a hydrogen atom ($-C(=NH)NH_2$).

[0112] All of the alkyl group, the cycloalkyl group, the alkenyl group, the alkynyl group, the aryl group, the heteroaryl group, and the group that can be represented by Formula (2) which can be employed as R^A may have a substituent. The substituent that R^A may have is not particularly limited, and examples thereof include an alkyl group, a cycloalkyl group, an alkenyl group, an alkynyl group, an aryl group, a heterocyclic group, an alkoxy group, an alkylthio group, an amino group, an alkylamino group, an arylamino group, an acyl group, an alkylcarbonyloxy group, an aryloxy group, an alkoxycarbonyl group, an aryloxycarbonyl group, an acylamino group, a sulfonamido group, a carbamoyl group, a sulfamoyl group, a halogen atom, a cyano group, a hydroxyl group, and a carboxy group. The respective substituents that R^A may have may be further substituted with a substituent.

[0113] The perovskite compound being used in the present invention has cations of a metallic atom other than elements belonging to Group I of the periodic table in the crystal structure. Examples of the metallic atom other than elements belonging to Group I of the periodic table include metallic atoms such as calcium (Ca), strontium (Sr), cadmium (Cd), copper (Cu), nickel (Ni), manganese (Mn), iron (Fe), cobalt (Co), palladium (Pd), germanium (Ge), tin (Sn), lead (Pb), ytterbium (Yb), europium (Eu), indium (In), titanium (Ti), and bismuth (Bi), among these, at least one selected from the group consisting of a Pb atom, a Cu atom, a Ge atom, and a Sn atom is more preferred, a Pb atom or a Sn atom is still more preferred, and a Pb atom is particularly preferred. The perovskite compound being used in the present invention may have one or two or more kinds of cations of metallic atoms other than elements belonging to Group I of the periodic table in the crystal structure. In the case of having two or more kinds of cations of metallic atoms other than elements belonging to Group I of the periodic table, the perovskite compound preferably has a Pb atom and a Sn atom. In a case in which the perovskite compound has two or more kinds of cations of metallic atoms other than elements belonging to Group I of the periodic table, the presence fractions of two or more kinds of these cations are not particularly limited.

[0114] At least some of the anions constituting the perovskite compound being used in the present invention are organic anions represented by Formula (An).

$$R^1\text{-}C(=X^1)\text{-}X^2 \qquad \text{Formula (An)}$$

[0115] In Formula (An), R^1 represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, a heteroaryl group, an aliphatic heterocyclic group, $-N(R^2)_2$, $-OR^3$, $-SR^4$, or a halogen atom. X^1 represents an O atom or a S atom and is preferably an O atom. R^2 to R^4 represent alkyl groups or aryl groups. X^2 represents O^- or S^- and is preferably O^-.

[0116] Here, in a case in which X^1 is an O atom and X^2 is O^-, the alkyl group that can be employed as R^1 is a substituted methyl group or an alkyl group having two or more carbon atoms. The alkyl group, the alkenyl group, and the alkynyl group which can be employed as R^1 may be linear or branched. In addition, in the present invention, examples of the substituent in the "substituted methyl group" do not include an alkyl group.

[0117] In a case in which X^1 is not an O atom or X^2 is not O^- (including a case in which X^1 is not an O atom and X^2 is not O^-), in the alkyl group that can be employed as R^1, the number of carbon atoms is preferably 1 to 30, more preferably 1 to 18, still more preferably 1 to 10, still more preferably 1 to 8, and still more preferably 1 to 6.

[0118] In a case in which X^1 is an O atom and X^2 is O^-, in the alkyl group having 2 or more carbon atoms which can be employed as R^1, the number of carbon atoms is preferably 2 to 30, more preferably 2 to 18, still more preferably 2 to 10, still more preferably 2 to 8, and still more preferably 2 to 6.

[0119] In a case in which R^1 is the substituted methyl group, the substituent in methyl is preferably a halogen atom, an alkenyl group, an alkynyl group, an aryl group, a heteroaryl group, an aliphatic heterocyclic group, a cyano group, a nitro group, an amino group, an imino group, an alkoxy group, a hydroxyl group, a thiol group, a sulfide group, an azo group, an azide group, or a carbonyl group, more preferably a halogen atom, and still more preferably a fluorine atom. In the substituted methyl group, the number of the substituents in methyl is preferably 1 to 3, more preferably 1 or 2, and still more preferably 1.

[0120] The alkenyl group, the alkynyl group, the aryl group, and the heteroaryl group which can be employed as R^1 are respectively the same as the alkenyl group, the alkynyl group, the aryl group, and the heteroaryl group which can be employed as R^A in Formula (1), and preferred aspects thereof are also identical.

[0121] In the aliphatic heterocyclic group that can be employed as R^1, the number of carbon atoms is preferably 0 to 24 and more preferably 1 to 18. Specific examples of preferred rings constituting the aliphatic heterocyclic group include a pyrrolidine ring, an oxolane ring, a thiolane ring, a piperidine ring, an oxane ring, a thiane ring, a piperazine ring, a morpholine ring, a quinuclidine ring, a pyrrolidine ring, an azetidine ring, an oxetane ring, an aziridine ring, a dioxane ring, a pentamethylene sulfide ring, and the like.

[0122] The alkyl group and the aryl group which can be employed as R^2 to R^4 are respectively the same as the alkyl group and the aryl group which can be employed as R^A in Formula (1), and preferred aspects thereof are also identical.

[0123] In Formula (An), R^1 is preferably an alkyl group, an aryl group, or a heteroaryl group, more preferably an aryl group or a heteroaryl group, and still more preferably an aryl group.

[0124] Specific preferred examples of the organic anion represented by Formula (An) will be illustrated below, but the present invention is not limited thereto.

A-1

A-2

A-3

A-4

A-5

A-6

A-7

A-8

A-9

A-10

A-11

A-12

A-13

A-14

A-15

[0125] The perovskite compound being used in the present invention preferably anions other than the organic anions represented by Formula (An) as anions. The anions other than the organic anions represented by Formula (An) may be monoatomic anions or polyatomic anions. Examples of the monoatomic anions include anions of a halogen atom. In addition, preferred examples of the polyatomic anions include NCS^- and NCO^-. Among these, the anions other than the organic anions represented by Formula (An) are preferably anions of a halogen atom. Examples of the halogen atom include a fluorine atom, a chlorine atom, a bromine atom, and an iodine atom, a bromine atom or an iodine atom is preferred, and an iodine atom is more preferred.

[0126] In the perovskite compound being used in the present invention, the molar ratio of the anions of the halogen atom to the organic anions represented by Formula (An) preferably satisfies Expression (i), more preferably satisfies Expression (ii), still more preferably satisfies Expression (iii), still more preferably satisfies Expression (iv), and still more preferably satisfies Expression (v).

Expression (i):

$$1 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 1659$$

Expression (ii):

$$32 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 829$$

Expression (iii):

$$32 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 414$$

Expression (iv):

$$32 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331$$

Expression (v):

$$54 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331$$

[0127] The perovskite compound that is used in the present invention has a perovskite-type crystal structure having the respective constituent ions described above. The perovskite compound that is used in the present invention is preferably a perovskite compound represented by Formula (I).

$$A_aM_mX_x \qquad \text{Formula (I)}$$

[0128] In the formula, A represents an element in Group I of the periodic table or a cationic organic group. M represents a metallic atom that is not an element in Group I of the periodic

[0129] table. X represents an anionic atom, anionic atomic group, or anionic organic group.

[0130] a represents 1 or 2, m represents 1, and a, m, and x satisfy a+2m=x.

[0131] In the present specification, the cationic organic group refers to an organic group being present as an organic cation in the perovskite-type crystal structure, the anionic atom refers to an atom being present as a monoatomic anion in the perovskite-type crystal structure, the anionic atomic group refers to an atomic group being present as a polyatomic anion in the perovskite-type crystal structure, and the anionic organic group refers to an organic group being present as

an organic anion in the perovskite-type crystal structure.

[0132] That is, in Formula (I), an element A belonging to Group I of the periodic table turns into and is present as a cation in the perovskite-type crystal structure.

[0133] In addition, in Formula (I), a cationic organic group A is present as the organic cation in the perovskite-type crystal structure.

[0134] In addition, in Formula (I), a metallic atom M is present in the perovskite-type crystal structure as the above-described cation of a metallic atom other than elements belonging to Group I of the periodic table.

[0135] In addition, in Formula (I), an anionic atom X is present as the monoatomic anion in the perovskite-type crystal structure.

[0136] In addition, in Formula (I), an anionic atom group X is present as the polyatomic anion in the perovskite-type crystal structure.

[0137] In addition, in Formula (I), an anionic organic group X is present as the organic anion in the perovskite-type crystal structure.

[0138] In the perovskite compound represented by Formula (I), at least a part of X is an anionic organic group guiding the organic anion represented by Formula (An).

[0139] The perovskite compound being used in the present invention may also be a mixture of a perovskite compound represented by Formula (1) in which a is 1 and a perovskite compound represented by Formula (I) in which a is 2.

[0140] The perovskite compound can be synthesized from MX_2 and AX. For example, the perovskite compound can be synthesized with reference to WO2014/097299A. In addition, the perovskite compound can be synthesized with appropriate reference to Akihiro Kojima, Kenjiro Teshima, Yasuo Shirai, and Tsutomu Miyasaka, "Organometal Halide Perovskites as Visible-Light Sensitizers for Photovoltaic Cells", J. Am. Chem. Soc., 2009, 131 (17), pp. 6050 and 6051.

[0141] In the perovskite compound being used in the present invention, the proportion of the total molar quantity of the cations of a metallic atom other than elements belonging to Group I of the periodic table and the organic cations of Formula (1) in the total molar quantity of the cations constituting the perovskite compound is preferably 90 to 100% by mol, more preferably 95 to 100% by mol, and still more preferably 98 to 100% by mol. In addition, in the perovskite compound being used in the present invention, the proportion of the total molar quantity of the organic anions represented by Formula (An) and the anions of the halogen atoms in the total molar quantity of the anions constituting the perovskite compound is preferably 90 to 100% by mol, more preferably 95 to 100% by mol, and still more preferably 98 to 100% by mol.

[0142] The amount of the light absorber used needs to be an amount at which, out of the surface of the porous layer 12 or the blocking layer 14, at least some of the surface on which light is incident is covered and is preferably an amount at which the surface is fully covered.

[0143] The content of the perovskite compound in the photosensitive layer 13 is generally 1 to 100% by mass.

<Hole transport layer 3>

[0144] The photoelectric conversion element of the present invention preferably has the hole transport layer 3 between the first electrode and the second electrode.

[0145] The hole transport layer 3 has a function of supplementing electrons to oxidants of the light absorber and is preferably a solid-form layer. The hole transport layer 3 is preferably provided between the photosensitive layer 13 in the first electrode 1 and the second electrode 2.

[0146] A hole-transporting material that forms the hole transport layer 3 is not particularly limited, and examples thereof include inorganic materials such as CuI and CuNCS, organic hole-transporting materials described in Paragraphs 0209 to 0212 of JP2001-291534A, and the like. Preferred examples of the organic hole-transporting material include conductive polymers such as polythiophene, polyaniline, polypyrrole, and polysilane, spiro compounds in which two rings share a central atom having a tetrahedral structure such as C or Si, aromatic amine compounds such as triarylamine, triphenylene compounds, nitrogen-containing heterocyclic compounds, and liquid-crystalline cyano compounds.

[0147] The hole-transporting material is preferably an organic hole-transporting material which can be applied in a solution and turns into solid, and examples thereof include 2,2',7,7'-tetrakis-(N,N-di-p-methoxyphenylamine)-9,9-spirobifluorene (also referred to as Spiro-OMeTAD), poly(3-hexylthiophene-2,5-diyl), 4-(diethylamino)benzoaldehyde, diphenylhydrazone, polyethylene dioxythiophene (PEDOT), and the like.

[0148] The film thickness of the hole transport layer 3 is not particularly limited, but is preferably 50 μm or less, more preferably 1 nm to 10 μm, still more preferably 5 nm to 5 μm, and particularly preferably 10 nm to 1 μm.

[0149] In the present invention, in a case in which the porous layer 12 is included, the total film thickness of the porous layer 12, the photosensitive layer 13, and the hole transport layer 3 is not particularly limited, but is, for example, preferably 0.1 to 200 μm, more preferably 0.2 to 50 μm, and still more preferably 0.3 to 5 μm.

<Electron transport layer 4>

[0150] In the present invention, as the photoelectric conversion element 10E, the electron transport layer 4 is preferably provided between the photosensitive layer 13C and the second electrode 2.

[0151] The electron transport layer 4 is the same as the electron transport layer 15 except for the fact that electrons are transferred to the second electrode and the electron transport layer is formed at a different location.

<Second electrode 2>

[0152] The second electrode 2 functions as a positive electrode in solar cells. The second electrode 2 is not particularly limited as long as the second electrode is conductive and, generally, can be provided with the same constitution as that of the conductive support 11. In a case in which a sufficient strength is maintained, the support 11a is not essentially required.

[0153] The structure of the second electrode 2 is preferably a structure having a strong power-collection effect. In order to allow light to reach the photosensitive layer 13, at least one of the conductive support 11 or the second electrode 2 needs to be substantially transparent. In the solar cell of the present invention, it is preferable that the conductive support 11 is transparent and sunlight enters the solar cell through the support 11a side. In this case, the second electrode 2 more preferably has a property of reflecting light.

[0154] Examples a material used to form the second electrode 2 include metal such as platinum (Pt), gold (Au), nickel (Ni), copper (Cu), silver (Ag), indium (In), ruthenium (Ru), palladium (Pd), rhodium (Rh), iridium (Ir), osmium (Os), and aluminum (Al), the above-described conductive metallic oxides, carbon materials, conductive polymers, and the like. The carbon materials need to be conductive materials formed of carbon atoms bonded together, and examples thereof include fullerene, carbon nanotubes, graphite, graphene, and the like.

[0155] The second electrode 2 is preferably a thin film (including a thin film obtained by means of vapor deposition) of metal or a conductive metallic oxide or a glass or plastic substrate having this thin film. The glass or plastic substrate is preferably a glass substrate having a gold or platinum thin film or a glass substrate on which platinum is vapor-deposited.

[0156] The film thickness of the second electrode 2 is not particularly limited, but is preferably 0.01 to 100 μm, more preferably 0.01 to 10 μm, and particularly preferably 0.01 to 1 μm.

<Other constitutions>

[0157] In the present invention, in order to prevent the first electrode 1 and the second electrode 2 from coming into contact with each other, a spacer or a separator can also be used instead of the blocking layer 14 and the like or together with the blocking layer 14 and the like.

[0158] In addition, a hole-blocking layer may be provided between the second electrode 2 and the hole transport layer 3.

<<Solar cell>>

[0159] The solar cell of the present invention is constituted using the photoelectric conversion element of the present invention. For example, as illustrated in Figs. 1 to 5, the photoelectric conversion element 10 constituted by providing the external circuit 6 can be used as a solar cell. As the external circuit which comes into contact with the first electrode 1 (the conductive support 11) and the second electrode 2, a well-known circuit can be used without any particular limitation.

[0160] In order to prevent the deterioration, evaporation, and the like of constituent substances, the solar cell of the present invention preferably has a side surface that is sealed with a polymer, an adhesive, or the like.

«Method for manufacturing photoelectric conversion element and solar cell»

[0161] The photoelectric conversion element and the solar cell of the present invention can be manufactured according to well-known manufacturing methods, for example, the methods described in WO2014/097299A.

[0162] Hereinafter, a method for manufacturing a photoelectric conversion element and a solar cell of the present invention will be briefly described.

[0163] The blocking layer 14, the porous layer 12, and at least one of the electron transport layer 15 or the hole transport layer 16 are formed on the surface of the conductive support 11 as desired.

[0164] The blocking layer 14 can be formed by, for example, applying a dispersion including the above-described insulating substance, a precursor compound thereof, or the like onto the surface of the conductive support 11 and firing the dispersion or thermally decomposing the dispersion by means of spraying.

[0165] A material used to form the porous layer 12 is preferably used in a fine particle form and more preferably used in a form of fine particles in a dispersion.

[0166] A method for forming the porous layer 12 is not particularly limited, and examples thereof include wet-type methods, dry-type methods, and other methods (for example, methods described in Chemical Review, Vol. 110, p. 6595 (published on 2010)). In these methods, it is preferable to apply the dispersion (paste) onto the surface of the conductive support 11 or the surface of the blocking layer 14 and then fire the dispersion at a temperature of 100°C to 800°C for ten minutes to ten hours. In such a case, it is possible to bring the fine particles into close contact with each other.

[0167] In a case in which firing is performed multiple times, the temperature of firing that is not the final firing (the non-final firing temperature) is preferably set to be lower than the temperature of the final firing (the final firing temperature). For example, in a case in which titanium oxide paste is used, the non-final firing temperature can be set in a range of 50°C to 300°C. In addition, the final firing temperature can be set to be higher than the non-firing firing temperature in a range of 100°C to 600°C. In a case in which a glass support is used as the support 11 a, the firing temperature is preferably 60°C to 500°C.

[0168] The amount of a porous material applied to form the porous layer 12 is appropriately set depending on the film thickness of the porous layer 12, the number of times of coating, and the like and is not particularly limited. The amount of the porous material applied to square meter of the surface area of the conductive support 11 is, for example, preferably 0.5 to 500 g and more preferably 5 to 100 g.

[0169] In a case in which the electron transport layer 15 or the hole transport layer 16 is provided, the layer can be formed in the same manner as the hole transport layer 3 or the electron transport layer 4 described below.

[0170] Next, the photosensitive layer 13 is provided.

[0171] A method for providing the photosensitive layer 13 is not particularly limited, and examples thereof include wet-type methods and dry-type methods. In the present invention, wet-type methods are preferred, and, for example, a method in which the surface is brought into contact with a light absorber solution including the absorber is preferred. In this method, first, the light absorber solution for forming the photosensitive layer 13 is prepared. The light absorber solution includes MX_2 and AX which are raw materials of the perovskite compound. Here, A, M, and X are the same as A, M, and X in Formula (I). In this light absorber solution, the molar ratio between MX_2 and AX is appropriately adjusted depending on the purpose. In a case in which a perovskite compound is formed as the light absorber, the molar ratio between MX_2 and AX is preferably 1:1 to 10:1. The light absorber solution can be prepared by mixing AX and MX_2 in a predetermined molar ratio and then, preferably, heating the components. This forming liquid is generally a solution, but may be a suspension. Heating conditions are not particularly limited, but the heating temperature is preferably 30°C to 200°C and more preferably 60°C to 150°C. The heating duration is preferably 0.5 to 100 hours and more preferably 1 to 3 hours. As a solvent or a dispersion medium, substances described below can be used.

[0172] Next, the prepared light absorber solution is brought into contact with the surface of a layer forming the photosensitive layer 13 on the surface thereof (in the photoelectric conversion element 10, any layer of the porous layer 12, the blocking layer 14, the electron transport layer 15, or the hole transport layer 16). Specifically, it is preferable to apply the light absorber solution onto the surface or immerse the surface in the forming liquid. Therefore, a perovskite compound is formed on the surface of the porous layer 12, the blocking layer 14, the electron transport layer 15, or the hole transport layer 16. The temperature at which the forming liquid is brought into contact with the surface is preferably 5°C to 100°C, and the immersion duration is preferably 5 seconds to 24 hours and more preferably 20 seconds to 1 hour. In a case in which the applied light absorber solution is dried, the forming liquid is preferably dried using heat and is generally dried by being generally heated at 20°C to 300°C and being preferably heated at 50°C to 170°C.

[0173] In addition, it is also possible to for the photosensitive layer according to a method for synthesizing the above-described perovskite compound.

[0174] Furthermore, examples thereof also include a method in which an AX solution including the AX and an MX_2 solution including the MX_2 are separately applied (including the immersion method) and are dried as necessary. In this method, any solution may be applied in advance, but the MX_2 solution is preferably applied in advance. In this method, the molar ratio between AX and MX_2, coating conditions, and drying conditions are the same as those in the above-described method. In this method, instead of applying the AX solution and the MX_2 solution, it is also possible to vapor-deposit AX or MX_2.

[0175] Furthermore, as another method, it is possible to use a dry-type method such as vapor deposition in a vacuum in which a compound or a mixture obtained by removing the solvent from the light absorber solution is used. For example, it is possible to use a method in which the AX and the MX_2 are simultaneously or sequentially vapor-deposited.

[0176] Therefore, the light absorber is formed and turns into the photosensitive layer 13.

[0177] On the photosensitive layer 13 provided as described above, preferably, the hole transport layer 3 or the electron transport layer 4 is formed.

[0178] The hole transport layer 3 can be formed by applying and drying a hole-transporting material solution including a hole-transporting material. In the hole-transporting material solution, the concentration of the hole-transporting material is preferably 0.1 to 1.0 M (mol/L) since coatability is excellent and, in a case in which the porous layer 12 is provided, the hole-transporting material is capable of easily intruding into the inside of pores in the porous layer 12.

[0179] The electron transport layer 4 can be formed by applying and drying an electron-transporting material solution

including an electron-transporting material.

[0180] After the hole transport layer 3 or the electron transport layer 4 is formed, the second electrode 2 is formed, thereby manufacturing the photoelectric conversion element and the solar cell.

[0181] The film thicknesses of the respective layers can be adjusted by appropriately changing the concentrations of the respective dispersion liquids or solutions and the number of times of coating. For example, in a case in which the photosensitive layers 13B and 13C having a thick film thickness are provided, the light absorber solution may be applied and dried multiple times.

[0182] The respective dispersion liquids and solutions described above may respectively include additives such as a dispersion aid and a surfactant.

[0183] Examples of the solvent or dispersion medium that is used in the method for manufacturing the photoelectric conversion element and the solar cell include solvents described in JP2001-291534A, but the solvent or dispersion medium is not limited thereto. In the present invention, organic solvents are preferred, and alcohol solvents, amide solvents, nitrile solvents, hydrocarbon solvents, lactone solvents, halogen solvents, sulfide solvents, and solvent mixtures of two or more thereof are preferred. The solvent mixture is preferably a solvent mixture of an alcohol solvent and a solvent selected from amide solvents, nitrile solvents, and hydrocarbon solvents. Specifically, methanol, ethanol, γ-butyrolactone, chlorobenzene, acetonitrile, dimethylformamide (DMF) or dimethylacetamide, or a solvent mixture thereof is preferred.

[0184] A method for applying the solutions or dispersants used to form the respective layers is not particularly limited, and it is possible to use a well-known coating method such as spin coating, extrusion die coating, blade coating, bar coating, screen printing, stencil printing, roll coating, curtain coating, spray coating, dip coating, an inkjet printing method, or an immersion method. Among these, spin coating, screen printing, an immersion method, and the like are preferred.

[0185] The photoelectric conversion element produced as described above can be used as a solar cell by connecting the external circuit 6 to the first electrode 1 and the second electrode 2.

[0186] Hereinafter, the present invention will be described in more detail on the basis of examples, but the present invention is not limited thereto.

Examples

Example and Comparative Example

[Manufacturing of photoelectric conversion element (Specimen No. 101)]

[0187] The photoelectric conversion element 10A illustrated in Fig. 1 was manufactured in an order described below. Meanwhile, in a case in which the film thickness of the photosensitive layer 13 is large, the photoelectric conversion element corresponds to the photoelectric conversion element 10B illustrated in Fig. 2.

<Production of conductive support 11>

[0188] A fluorine-doped SnO_2 conductive film (the transparent electrode 11b) was formed on a glass substrate (the support 11a, thickness: 2.2 mm), thereby producing a conductive support 11.

<Preparation of solution for blocking layer>

[0189] An isopropanol solution containing 15% by mass of titanium diisopropoxide bis(acetylacetonate) (manufactured by Sigma-Aldrich Japan K.K.) was diluted with 1-butanol, thereby preparing 0.02 M of a solution for a blocking layer.

<Formation of blocking layer 14>

[0190] A blocking layer 14 made of titanium oxide (having a film thickness of 50 nm) was formed on the SnO_2 conductive film of the conductive support 11 using 0.02 M of the solution for the blocking layer at 450°C by means of a spray thermal decomposition method.

<Preparation of titanium oxide paste>

[0191] Ethyl cellulose, lauric acid, and terpineol were added to an ethanol dispersion liquid of titanium oxide (anatase, an average particle diameter of 20 nm), thereby preparing titanium oxide paste.

<Formation of porous layer 12>

[0192] The prepared titanium oxide paste was applied onto the blocking layer 14 by means of a screen printing method and was fired. The application and firing of the titanium oxide paste were repeated again. Meanwhile, the first firing was carried out at 130°C for one hour, and the second firing was carried out at 500°C for one hour. The obtained titanium oxide fired body was immersed in an aqueous solution of 40 mM of $TiCl_4$, then, was heated at 60°C for one hour, and, continuously, was heated at 500°C for 30 minutes, thereby forming the porous layer 12 (having a film thickness of 250 nm) made of TiO_2.

<Formation of photosensitive layer 13A>

[0193] A 40% methanol solution of methyl amine (27.86 mL) and an aqueous solution of 57% by mass of hydrogen iodide (hydroiodic acid, 30 mL) were stirred in a flask at 0°C for two hours and then condensed, thereby obtaining a CH_3NH_3I coarse body. The obtained CH_3NH_3I coarse body was dissolved in ethanol and was recrystallized with diethyl ether. The precipitated crystals were filtered and were dried at 60°C for 24 hours under reduced pressure, thereby obtaining purified CH_3NH_3I.

[0194] A 9.8 mol/L methanol solution of methylamine (10 mL) and Anionic Organic Compound A-1-1 (8.6 g) were mixed together, thereby obtaining a solution (hereinafter, referred to as "A-1-1/methylamine solution") of a compound obtained by bonding anions (A-1-1) of Compound A-1-1 and $CH_3NH_3^+$ at a molar ratio of 1:1 (hereinafter, referred to as "A-1-1/methylamine compound").

[0195] Next, the purified CH_3NH_3I, an A-1-1/methylamine solution, and PbI_2 were stirred and mixed together in DMF at 40°C for five hours at molar ratios among CH_3NH_3I, an A-1-1/methylamine compound, and PbI_2 set to 97:3:33 and then filtered using a polytetrafluoroethylene (PTFE) syringe filter, thereby preparing 40% by mass of a light absorber solution A.

[0196] The prepared light absorber solution A was applied onto the porous layer 12 using a spin coating method (at 3,000 rpm for 60 seconds), and the light absorber solution A was dried at 100°C for 80 minutes using a hot plate, thereby forming a photosensitive layer A (having a film thickness of 300 nm (including the film thickness of the porous layer 12 of 250 nm)) as the photosensitive layer 13A having a perovskite compound.

[0197] A first electrode 1 was produced in the above-described manner.

A — 1 — 1

<Preparation of hole-transporting material solution>

[0198] Spiro-OMeTAD (180 mg) as a hole-transporting material was dissolved in chlorobenzene (1 mL). An acetonitrile solution (37.5 μL) obtained by dissolving lithium-bis(trifluoromethanesulfonyl)imide (170 mg) in acetonitrile (1 mL) and t-butylpyridine (TBP, 17.5 μL) were added to and mixed with the chlorobenzene solution, thereby preparing a hole-transporting material solution.

<Formation of hole transport layer 3>

[0199] Next, the hole-transporting material solution was applied onto the photosensitive layer 13 in the first electrode 1 using a spin coating, and the applied hole-transporting material solution was dried, thereby forming a hole transport layer 3 (film thickness: 0.1 μm).

<Production of second electrode 2>

[0200] Gold (film thickness: 0.1 μm) was vapor-deposited on the hole transport layer 3 using a vapor deposition method, thereby producing a second electrode 2.

[0201] A photoelectric conversion element 10 with Specimen No. 101 was manufactured in the above-described manner.

[Manufacturing of photoelectric conversion element (Specimen No. 102)]

[0202] A photoelectric conversion element 10 with Specimen No. 102 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, Anionic Compound A-1-1 was changed to Anionic Compound A-2-1.

A－2－1

[Manufacturing of photoelectric conversion element (Specimen No. 103)]

[0203] A photoelectric conversion element 10 with Specimen No. 103 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, Anionic Compound A-1-1 was changed to Anionic Compound A-3-1.

A－3－1

[Manufacturing of photoelectric conversion element (Specimen No. 104)]

[0204] A photoelectric conversion element 10 with Specimen No. 104 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 95:5:33.

[Manufacturing of photoelectric conversion element (Specimen No. 105)]

[0205] A photoelectric conversion element 10 with Specimen No. 105 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 99.5:0.5:33.

[Manufacturing of photoelectric conversion element (Specimen No. 106)]

[0206] A photoelectric conversion element 10 with Specimen No. 106 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, ethylamine was used instead of methylamine.

[Manufacturing of photoelectric conversion element (Specimen No. 107)]

[0207] A photoelectric conversion element 10 with Specimen No. 107 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-2-1.

[Manufacturing of photoelectric conversion element (Specimen No. 108)]

[0208] A photoelectric conversion element 10 with Specimen No. 108 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-3-1.

[Manufacturing of photoelectric conversion element (Specimen No. 109)]

[0209] A photoelectric conversion element 10 with Specimen No. 109 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 104 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 104, Anionic Compound A-1-1 was changed to Anionic Compound A-2-1.

[Manufacturing of photoelectric conversion element (Specimen No. 110)]

[0210] A photoelectric conversion element 10 with Specimen No. 110 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 104 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 104, Anionic Compound A-1-1 was changed to Anionic Compound A-3-1.

[Manufacturing of photoelectric conversion element (Specimen No. 111)]

[0211] A photoelectric conversion element 10 with Specimen No. 111 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-8-1.

A－8－1

[Manufacturing of photoelectric conversion element (Specimen No. 112)]

[0212] A photoelectric conversion element 10 with Specimen No. 112 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-12-1.

A－12－1

[Manufacturing of photoelectric conversion element (Specimen No. 113)]

[0213] A photoelectric conversion element 10 with Specimen No. 113 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-14-1.

A－14－1

[Manufacturing of photoelectric conversion element (Specimen No. 114)]

[0214] A photoelectric conversion element 10 with Specimen No. 114 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-17-1.

A－17－1

[Manufacturing of photoelectric conversion element (Specimen No. 115)]

[0215] A photoelectric conversion element 10 with Specimen No. 115 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-18-1.

A－18－1

[Manufacturing of photoelectric conversion element (Specimen No. 116)]

[0216] A photoelectric conversion element 10 with Specimen No. 116 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-19-1.

A－19－1

[Manufacturing of photoelectric conversion element (Specimen No. 117)]

[0217] A photoelectric conversion element 10 with Specimen No. 117 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-20-1.

A－20－1

[Manufacturing of photoelectric conversion element (Specimen No. 118)]

[0218] A photoelectric conversion element 10 with Specimen No. 118 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 105 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 105, Anionic Compound A-1-1 was changed to Anionic Compound A-21-1.

A－21－1

[Manufacturing of photoelectric conversion element (Specimen No. 119)]

[0219] A photoelectric conversion element 10 with Specimen No. 119 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 99.75:0.25:33.

[Manufacturing of photoelectric conversion element (Specimen No. 120)]

[0220] A photoelectric conversion element 10 with Specimen No. 120 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 99.4:0.6:33.

[Manufacturing of photoelectric conversion element (Specimen No. 121)]

[0221] A photoelectric conversion element 10 with Specimen No. 121 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 94.5:5.5:33.

[Manufacturing of photoelectric conversion element (Specimen No. 122)]

[0222] A photoelectric conversion element 10 with Specimen No. 122 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 95.8:4.2:33.

[Manufacturing of photoelectric conversion element (Specimen No. 123)]

[0223] A photoelectric conversion element 10 with Specimen No. 123 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation

of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 were mixed at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 99:1:33.

[Manufacturing of photoelectric conversion element (Specimen No. 201)]

[0224] A photoelectric conversion element 10 with Specimen No. 201 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, Anionic Compound A-1-1 was changed to acetic acid.

[Manufacturing of photoelectric conversion element (Specimen No. 202)]

[0225] A photoelectric conversion element 10 with Specimen No. 202 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, Anionic Compound A-1-1 was changed to formic acid.

[Manufacturing of photoelectric conversion element (Specimen No. 203)]

[0226] A photoelectric conversion element 10 with Specimen No. 203 was manufactured in the same manner as in the manufacturing of the photoelectric conversion element with Specimen No. 101 except for the fact that, in the <formation of photosensitive layer 13A> during the manufacturing of the above-described photoelectric conversion element with Specimen No. 101, instead of mixing the purified CH_3NH_3I, the A-1-1/methylamine solution, and PbI_2 at molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2 set to 97:3:33, the A-1-1/methylamine compound was not used, and CH_3NH_3I and PbI_2 were mixed together at a molar ratio between CH_3NH_3I and PbI_2 set to 100:33.

[Evaluation of moisture resistance and moisture resistance unevenness]

<Measurement of initial photoelectric conversion efficiency>

[0227] Photoelectric conversion efficiencies were evaluated in the following manner.

[0228] Ten testing pieces of the photoelectric conversion element with each specimen number were manufactured. Cell characteristics testing was carried out on the ten testing pieces respectively, and photoelectric conversion efficiencies (η/%) were measured. In addition, the average value of the values of these ten testing pieces was considered as the initial photoelectric conversion efficiency (η/%) of the photoelectric conversion element with each specimen number. The cell characteristics testing was carried out by radiating 1,000 W/m^2 of quasi-sunlight from a xenon lamp through an AM1.5 filter using a solar simulator "WXS-85H" (Wacom). Current-voltage characteristics were measured using an I-V tester, and photoelectric conversion efficiencies (η/%) were obtained.

<Evaluation of moisture resistance>

[0229] The moisture resistance of the photoelectric conversion element was measured in the following manner.

[0230] Ten testing pieces of each specimen number were stored in a constant temperature and humidity tank with a temperature of 35°C and a humidity of 55%RH for 24 hours respectively, cell characteristics testing was carried out in the same manner as described above, and photoelectric conversion efficiencies (η/%) were measured.

[0231] The average value of the values of the ten testing pieces was considered as the photoelectric conversion efficiency (η/%) of the photoelectric conversion element with each specimen number after the storage.

[0232] The moisture resistance of the photoelectric conversion element was evaluated on the basis of the decline percentage of the photoelectric conversion efficiency computed using the following expression.

$$\text{Decline percentage (\%)} = 100 - \{100 \times (\text{photoelectric conversion efficiency after storage}) / (\text{initial photoelectric conversion efficiency})\}$$

[0233] In all of the photoelectric conversion elements with Specimen Nos. 101 to 123 (photoelectric conversion elements in which the perovskite compound had the organic anions determined in the present invention), the decline

percentages of the photoelectric conversion efficiency computed using the above-described expression were all suppressed at less than 40%, and favorable moisture resistance was exhibited. On the other hand, in the photoelectric conversion elements with Specimen Nos. 201, 202, and 203 (photoelectric conversion elements in which the perovskite compound did not have the organic anions determined in the present invention), the decline percentages of the photoelectric conversion efficiency computed using the above-described expression exceeded 40%, and moisture resistance was poor.

<Evaluation of moisture resistance unevenness>

[0234] Ten testing pieces of the photoelectric conversion element with each specimen number were manufactured. For each of the ten testing specimens, the decline percentage of the photoelectric conversion efficiency (Decline percentage (%)=100-{100xIS/1E}) was computed from the initial photoelectric conversion efficiency immediately after being manufactured (IE) and the photoelectric conversion efficiency after being stored in a constant temperature and humidity tank with a temperature of 35°C and a humidity of 55%RH for 24 hours (IS). A value obtained by subtracting the decline percentage of the photoelectric conversion element having the minimum decline percentage out of the ten testing specimens (the minimum decline percentage) from the decline percentage of the photoelectric conversion element having the maximum decline percentage out of the ten testing specimens (the maximum decline percentage) was considered as "decline percentage unevenness", and moisture resistance unevenness was evaluated on the basis of the following standards.

- Evaluation standards of moisture resistance unevenness-

[A]:

[0235] The decline percentage unevenness is less than 10%

[B+):

[0236] [A] is not satisfied, and the decline percentage unevenness is less than 14%

[B]:

[0237] [A] and [B+] are not satisfied, and the decline percentage unevenness is less than 18%

[C+]:

[0238] [A], [B+], and [B] are all not satisfied, and the decline percentage unevenness is less than 22%

[C]:

[0239] [A], [B+], [B], and [C+] are all not satisfied, and the decline percentage unevenness is less than 26%

[D]:

[0240] [A], [B+], [B], [C+], and [C] are all not satisfied
In the evaluation of moisture resistance unevenness, [A], [B+], [B], [C+], and [C] are pass levels, [A], [B+], or [B] is preferred, and [A] is more preferred. On the other hand, at [D] level, moisture resistance unevenness is significant among the elements, and the moisture resistance unevenness fails to reach the pass level (required level) of the present invention.
[0241] The results are shown in Table 1.
[0242] Meanwhile, "Anions of halogen atom/organic anions (molar ratio in perovskite compound)" in Table 1 can be computed from, when A-1-1 is used as the anionic organic compound, the above-described mixing molar ratios among CH_3NH_3I, the A-1-1/methylamine compound, and PbI_2, mixing molar ratios among $CH_3CH_2NH_3I$, the A-1-1/ethylamine compound, and PbI_2, mixing molar ratios among CH_3NH_3I, the acetic acid/methylamine compound, and PbI_2, or mixing molar ratios among CH_3NH_3I, the formic acid/methylamine compound, and PbI_2.
[0243] In addition, even in a case in which the organic anions represented by Formula (An) other than A-1-1 are used as the anionic organic compound, similarly, "Anions of halogen atom/organic anions (molar ratio in perovskite compound)" can be computed from the mixing molar ratio.

[Table 1]

Specimen Nos.	R^A-NH_3I	Anionic organic compound	Anions of halogen atom/ organic anions (molar ratio in perovskite compound)	Unevenness in photoelectric conversion efficiency	
101	CH_3NH_3I	A-1-1	54	[B+]	Present Invention
102	CH_3NH_3I	A-2-1	54	[B+]	Present Invention
103	CH_3NH_3I	A-3-1	54	[A]	Present Invention
104	CH_3NH_3I	A-1-1	32	[C+]	Present Invention
105	CH_3NH_3I	A-1-1	331	[B+]	Present Invention
106	$CH_3CH_2NH_3I$	A-1-1	331	[B+]	Present Invention
107	CH_3NH_3I	A-2-1	331	[B^+]	Present Invention
108	CH_3NH_3I	A-3-1	331	[A]	Present Invention
109	CH_3NH_3I	A-2-1	32	[C+]	Present Invention
110	CH_3NH_3I	A-3-1	32	[B+]	Present Invention
111	CH_3NH_3I	A-8-1	331	[B]	Present Invention
112	CH_3NH_3I	A-12-1	331	[A]	Present Invention
113	CH_3NH_3I	A-14-1	331	[A]	Present Invention
114	CH_3NH_3I	A-17-1	331	[B+]	Present Invention
115	CH_3NH_3I	A-18-1	331	[B]	Present Invention
116	CH_3NH_3I	A-19-1	331	[B+]	Present Invention
117	CH_3NH_3I	A-20-1	331	[A]	Present Invention
118	CH_3NH_3I	A-21-1	331	[B+]	Present Invention
119	CH_3NH_3I	A-1-1	663	[B]	Present Invention
120	CH_3NH_3I	A-1-1	276	[B+]	Present Invention
121	CH_3NH_3I	A-1-1	29	[C]	Present Invention

(continued)

Specimen Nos.	R^A-NH_3I	Anionic organic compound	Anions of halogen atom/ organic anions (molar ratio in perovskite compound)	Unevenness in photoelectric conversion efficiency	
122	CH_3NH_3I	A-1-1	39	[C+]	Present Invention
123	CH_3NH_3I	A-1-1	165	[B+]	Present Invention
201	CH_3NH_3I	Acetic acid	54	[D]	Comparative Examples
202	CH_3NH_3I	Formic acid	54	[D]	Comparative Example
203	CH_3NH_3I	None	- Example	[D]	Comparative Example

[0244] As described above, in a case in which the perovskite compound in the light absorber did not include the organic anions represented by Formula (An) in the crystal structure, the moisture resistance was poor, and furthermore, moisture resistance unevenness was significant among photoelectric conversion elements manufactured under the same conditions (Specimen Nos. 201 to 203).

[0245] In contrast, in a case in which the perovskite compound in the light absorber included the organic anions represented by Formula (An) in the crystal structure, the moisture resistance improved, and it was possible to suppress moisture resistance unevenness was significant among photoelectric conversion elements manufactured under the same conditions (Specimen Nos. 101 to 123). That is, it was found that, when the perovskite compound in the light absorber includes the organic anions represented by Formula (An) in the crystal structure, moisture resistance unevenness is significantly suppressed among photoelectric conversion elements to be obtained, and it is possible to manufacture photoelectric conversion elements having uniform qualities.

[0246] The present invention has been described together with embodiments thereof and drawings, but the present inventors do not limit the present invention in any detailed part of the description unless particularly otherwise described and consider that the present invention is supposed to be widely interpreted within the scope of the concept of the present invention which is described in the accompanying claims.

[0247] The present application claims priority on the basis of JP2015-045168, filed on March 6, 2015 and JP2016-010696, filed on January 22, 2016, the contents of which are incorporated herein by reference.

Explanation of References

[0248]

1A, 1B, 1C, 1D, 1E: first electrode
11: conductive support
11a: support
11b: transparent electrode
12: porous layer
13A, 13B, 13C: photosensitive layer
14: blocking layer
15: electron transport layer
16: hole transport layer
2: second electrode
3A, 3B: hole transport layer
4: electron transport layer
6: external circuit (lead)
10A, 10B, 10C, 10D, 10E: photoelectric conversion element
100A, 100B, 100C, 100D, 100E: system in which photoelectric conversion element is applied as cell
M: electric motor

Claims

1. A photoelectric conversion element comprising:

   a first electrode having a photosensitive layer including a light absorber on a conductive support; and
   a second electrode facing the first electrode,
   wherein the light absorber includes a compound having a perovskite-type crystal structure including cations of an element belonging to Group I of the periodic table or organic cations, cations of a metallic atom other than elements belonging to Group I of the periodic table, and anions, and
   at least some of the anions constituting the compound are organic anions represented by Formula (An),

   $$R^1\text{-}C(=X^1)\text{-}X^2 \qquad \text{Formula (An)}$$

   in the formula, R^1 represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, a heteroaryl group, an aliphatic heterocyclic group, $-N(R^2)_2$, $-OR^3$, $-SR^4$, or a halogen atom, X^1 represents an O atom or a S atom, R^2 to R^4 represent alkyl groups or aryl groups, and X^2 represents O^- or S^-,
   here, in a case in which X^1 is an O atom and X^2 is O^-, the alkyl group is a substituted methyl group or an alkyl group having two or more carbon atoms.

2. The photoelectric conversion element according to claim 1,

   wherein X^1 represents an O atom, and X^2 represents O^-.

3. The photoelectric conversion element according to claim 1 or 2,

   wherein R^1 is an aryl group or a heteroaryl group.

4. The photoelectric conversion element according to any one of claims 1 to 3,

   wherein the compound having a perovskite-type crystal structure has anions of a halogen atom.

5. The photoelectric conversion element according to claim 4,

   wherein, in the compound having a perovskite-type crystal structure, a molar ratio of the anions of a halogen atom to the organic anions represented by Formula (An) satisfies the following expression,

   $$32 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331.$$

6. The photoelectric conversion element according to claim 5,

   wherein, in the compound having a perovskite-type crystal structure, the molar ratio of the anions of a halogen atom to the organic anions represented by Formula (An) satisfies the following expression,

   $$54 \leq [\text{anions of halogen atom}]/[\text{organic anions represented by Formula (An)}] \leq 331.$$

7. A solar cell using the photoelectric conversion element according to any one of claims 1 to 6.

FIG. 1

100A
10A
2
6
3A
13A
12
14
1A
M
11b
11
11a
e⁻

FIG. 2

100B
10B
2
6
3B
13B
12
14
1B
M
11b
11
11a
e⁻

FIG. 3

FIG. 4

FIG. 5

INTERNATIONAL SEARCH REPORT

International application No.
PCT/JP2016/055519

A. CLASSIFICATION OF SUBJECT MATTER
H01L51/44(2006.01)i, *H01G9/20*(2006.01)i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
H01L51/44, H01G9/20

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Jitsuyo Shinan Koho	1922-1996	Jitsuyo Shinan Toroku Koho	1996-2016
Kokai Jitsuyo Shinan Koho	1971-2016	Toroku Jitsuyo Shinan Koho	1994-2016

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
Scopus IEEE Xplore

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	WO 2015/16114 A1 (Fujifilm Corp.), 05 February 2015 (05.02.2015), paragraphs [0060] to [0108], [0131] to [0162] & JP 2015-46582 A & TW 201507241 A	1-7
A	JP 2015-211213 A (National Central University), 24 November 2015 (24.11.2015), paragraphs [0019] to [0038] & US 2015/0311364 A1 paragraphs [0020] to [0047] & EP 2940751 A2 & TW 201540691 A & TW 00I474992 B	1-7

☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.

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"&" document member of the same patent family

Date of the actual completion of the international search	Date of mailing of the international search report
07 April 2016 (07.04.16)	19 April 2016 (19.04.16)
Name and mailing address of the ISA/ Japan Patent Office 3-4-3,Kasumigaseki,Chiyoda-ku, Tokyo 100-8915,Japan	Authorized officer Telephone No.

Form PCT/ISA/210 (second sheet) (January 2015)

REFERENCES CITED IN THE DESCRIPTION

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